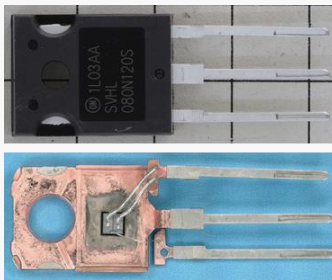
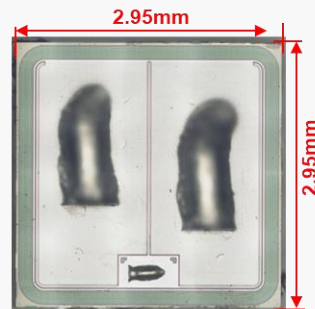


## On Semiconductor SiC-MOSFET NVHL080N120SC1 Die Structure and Process Analysis Reports

**September 2019.** LTEC Corporation released detailed structure and process analysis reports of the ON-Semiconductor 1200V SiC MOSFET.



Package



Die image

### Product overview

In March 2019, ON-Semiconductor announced production of their 1200V,  $R_{on}=80m\Omega$  and  $DC I_d=20A$  SiC MOSFET, promising high power density and high efficiency. These features reduce the need for thermal management, BOM cost, size and weight. **The analyzed product (NVHL080N120SC1) is AEC-Q101 qualified for stringent automotive applications.**

### Report contents and price

#### ○ SiC-MOSEFT structural analysis report: \$6,000

- Package appearance, package cross-section analysis, EDX material analysis
- SiC-MOSFET die plane analysis, layout
- SiC-MOSFET die cross-section analysis, Cell part, die edge

#### ○ SiC-MOSFET process and device characteristics analysis report: \$4,600

- Estimation of SiC-MOSFET manufacturing process flow and schematic flow cross section based on structural analysis results
- Electrical characteristics evaluation and correlation with structural parameters

Contact LTEC Corporation for the current price as it decreases over time

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